

ACIDIC POST-CMP CLEANING COMPOSITION

ABSTRACT OF THE DISCLOSURE

An acidic post-CMP cleaning composition includes at least one polyamino-polycarboxylic acid, or salt thereof; at least one hydroxycarboxylic acid, or salt thereof; and the remainder being substantially water. The acidic cleaning composition also includes a surfactant. The acidic post-CMP cleaning composition has a pH of 1 to 5, and is useful for removing the contaminants from the wafer surface after a CMP process without making roughness worse.